

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 63-266814

(43)Date of publication of application : 02.11.1988

(51)Int.Cl.

H01L 21/205

(21)Application number : 62-099893

(71)Applicant : NEC CORP

(22)Date of filing : 24.04.1987

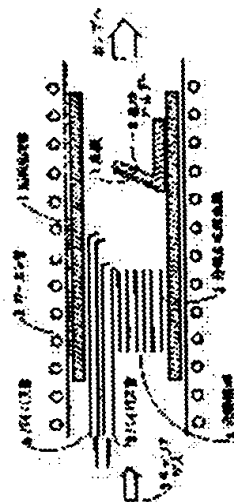
(72)Inventor : MORI KAZUO
YOSHIDA MASAJI

(54) FORMING METHOD FOR AL III-V COMPOUND SEMICONDUCTOR THIN FILM

(57)Abstract:

PURPOSE: To form an superthin film of Al III-V compound semiconductor by an atomic layer epitaxy by supplying in advance Al organic compound to a decomposing area to decompose the compound, condensing and removing generated sole aluminum, and then supplying the decomposed gas onto a substrate.

CONSTITUTION: A carbon tube 2 is mounted in a quartz reaction tube 1, and set at a predetermined temperature. Hydrogen gas of carrier gas 3 is fed from left to right to transport $\text{Al}(\text{C}_2\text{H}_5)_2\text{Cl}$. Carbon decomposition reaction accelerating plates 5 are arranged on a decomposing area 4 at the upstream of a substrate in the tube 2, and a carbon substrate holder 6 for placing the substrate 7 is provided at the downstream of the area. Then, above semiconductor thin film forming apparatus is used to grown AlAs on the substrate, AsH_3 is introduced as group V element gaseous compound through a carbon bypass tube 8 bypassing the decomposing area to the periphery of the substrate. Thus, the extremely thin film of Al III-V compound semiconductor can be formed under good controllability.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]